

Kanto Gakuin University
Materials & Surface Engineering Research Center
Technology Report

- △ Potential Applications
- △ Plating on Glass/Silicon
- △ Direct Patterning
- △ Non-toxic Gold (RSG) Plating System

2013年2月15日
Chris Cordonier

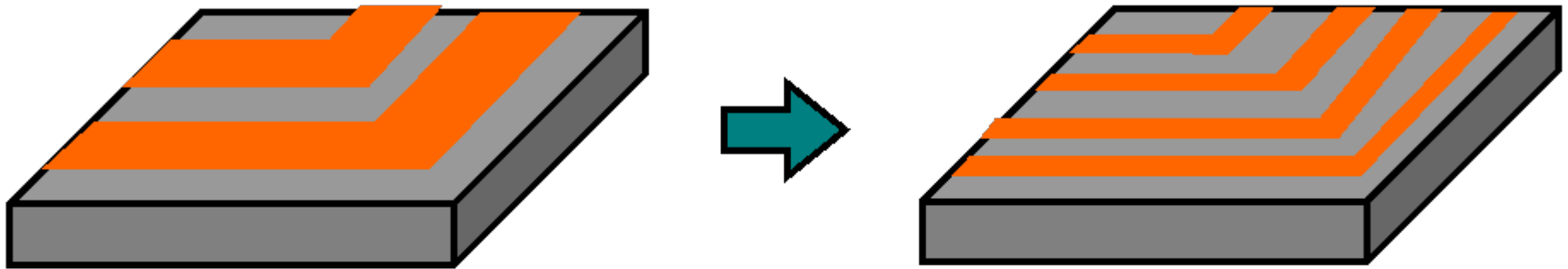
Potential Applications

for

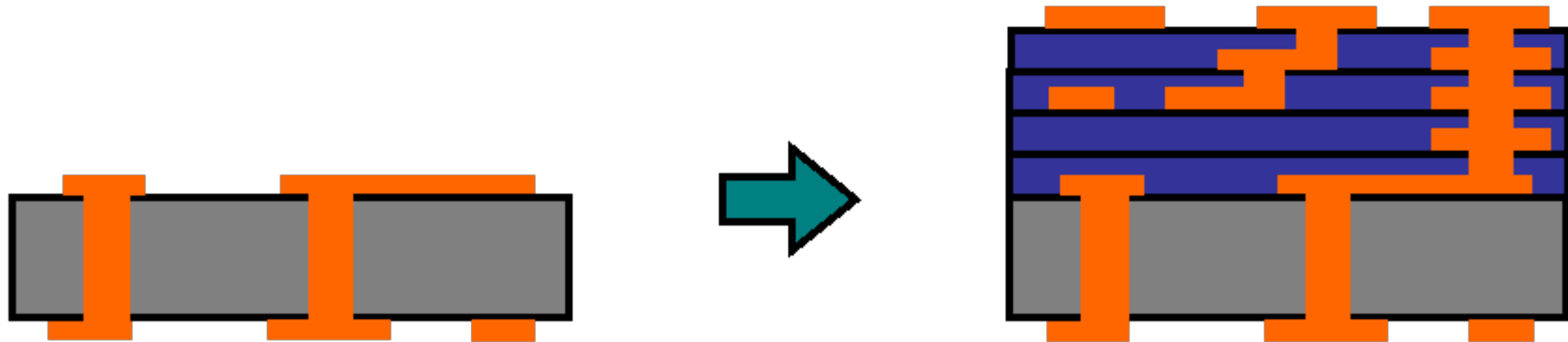
plating on glass & fine patterning (< 5 μm)

Future Generation Circuitry

- **Smaller:** Finer pitch, smaller features, more precise shapes



- **More stacking:** More layer substrate & stacked devices (3D LSI)

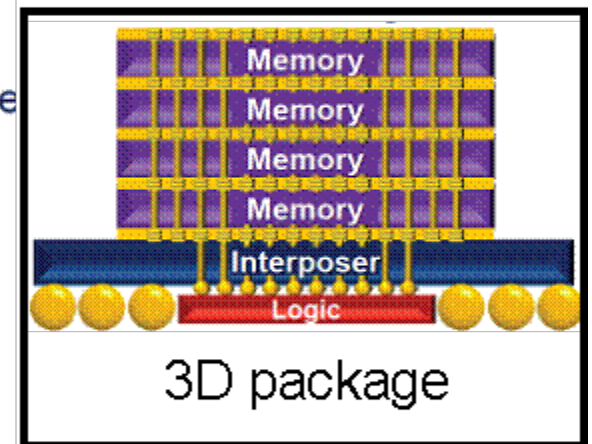
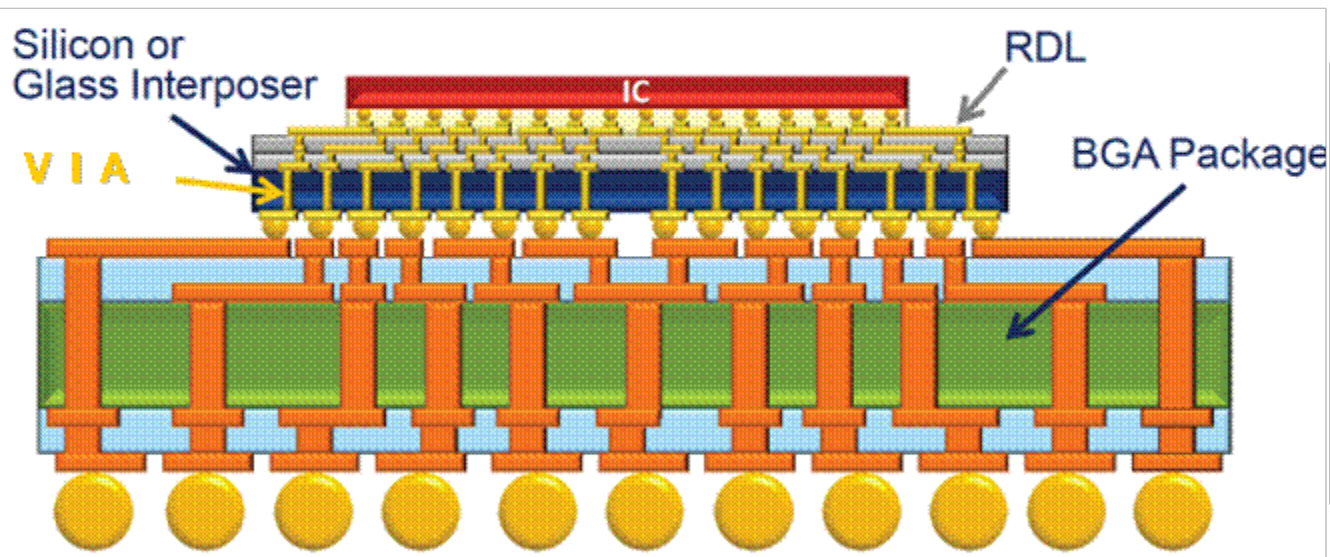


- **Lower cost**
- **Green:** Environmentally benign chemistry, process, materials, minimal waste

Glass Interposer

Direct pattern seed layer plating for interposer/RDL:

- Solution deposition of copper or gold seed layer to glass substrate with via holes. *Surface & inside via holes*



Silicon → GLASS interposer:

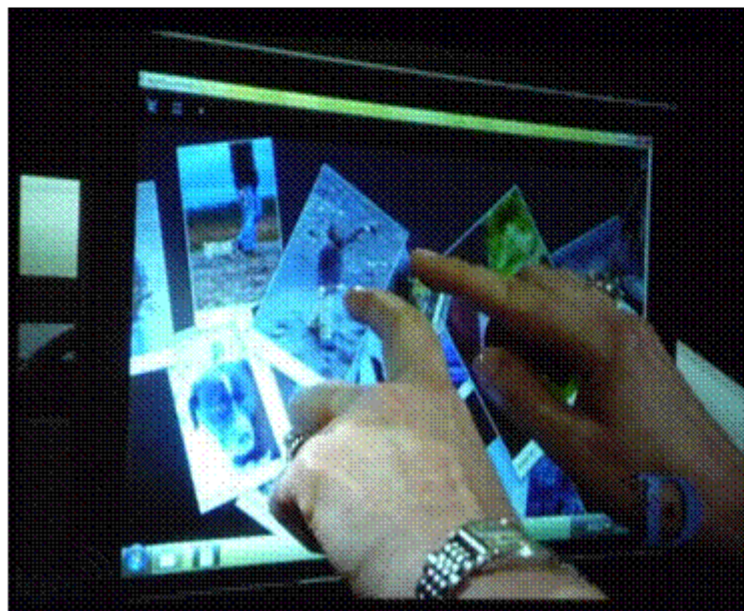
- low latency, strong insulation
- low cost, easy handling
- large area / roll to roll processing

Optical Electronics

- △ Displays (fine circuitry)
- △ Optical transmission
- △ LED & Organic electroluminescent illumination (electrodes)
- △ Touch panels (electrodes)
- △ Photovoltaics

electrical conductor + transparent \Rightarrow transparent electrode

Windows 7



Smart phone / Tablet
display + touch panel



Conventional: sputtered tin doped indium oxide (ITO) or fine metal wires (>5 μm)

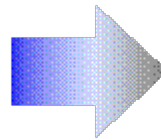
Transparent Electrodes

transparent electrodes for
capacitive type touch panels

tin doped indium oxide

(+)
transparency
stability

(-)
expensive
environmental
impact



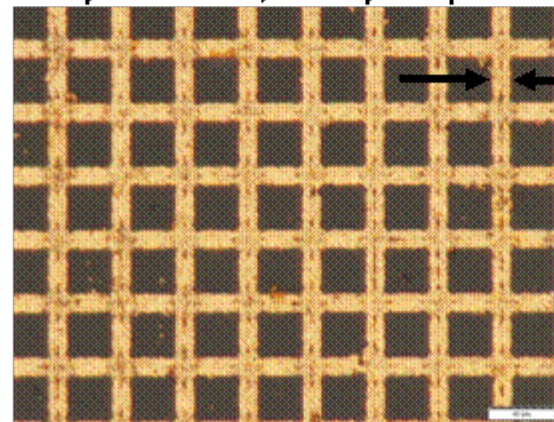
fine metal mesh wiring

(+)
conductivity
inexpensive

(-)
not
transparent

fine
pattern

electroless Cu on
patterned Cu catalyst mesh
2 μ m wire / 10 μ m pitch

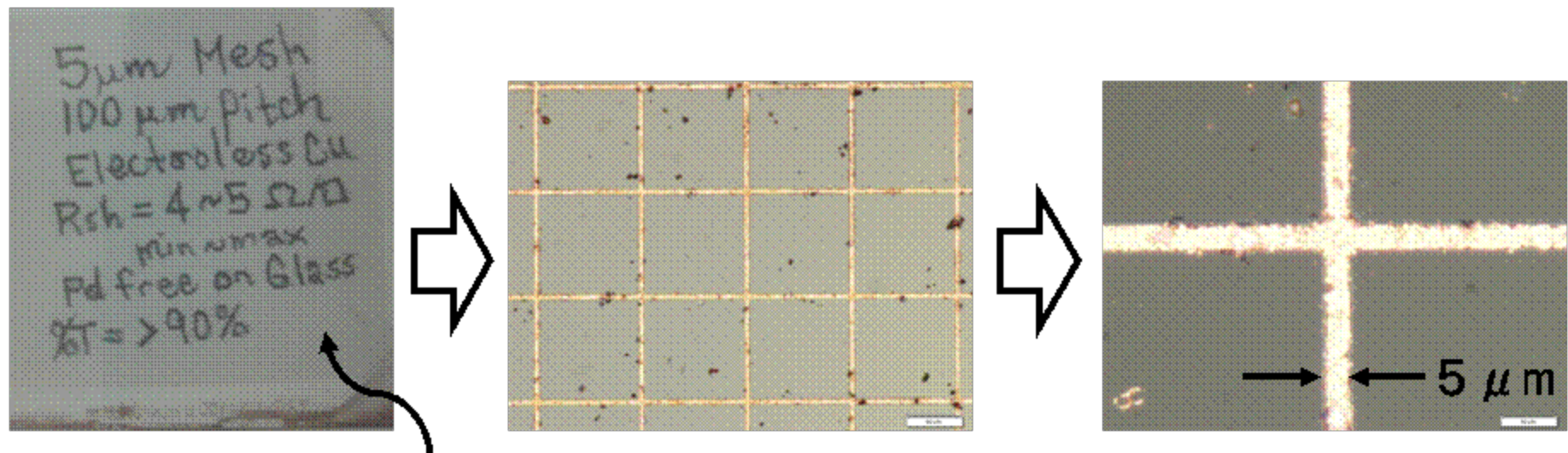


2 μ m

Current technology is $\sim 10 \mu$ m,
& 5 μ m rumors
but not invisible
 \Rightarrow Use $< 5 \mu$ m lines.

Mesh Pattern / Transparent Electrode

Patterned copper on copper catalyst



Fine mesh as a transparent electrode

“More conductive than ITO with the same transparency”

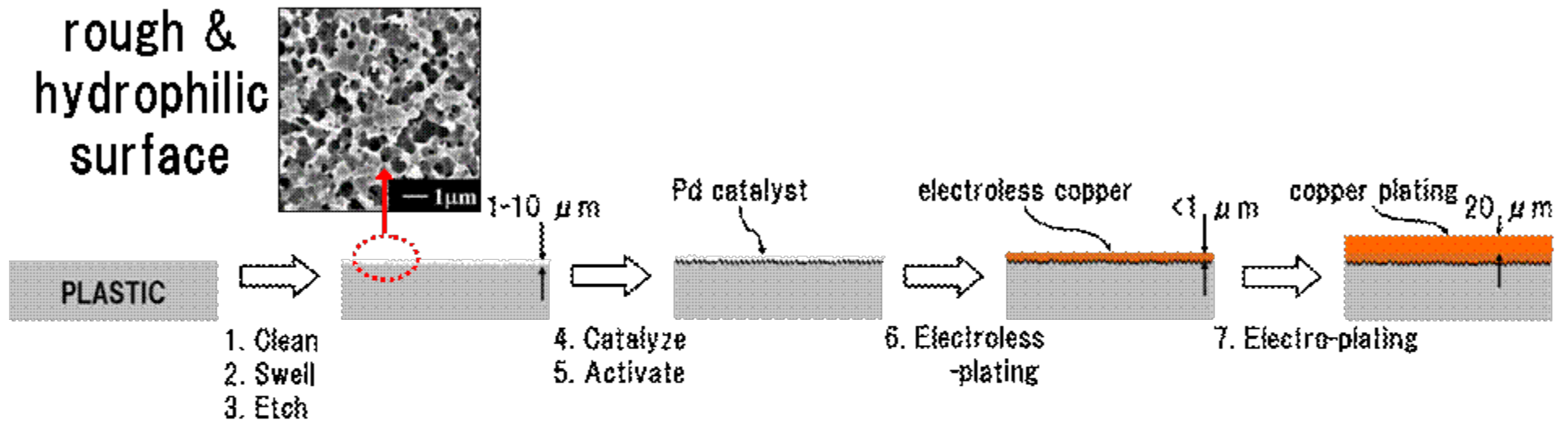
Sheet resistance, $R_{sh} = 0.5-5 \Omega/\square$, Transparency, $\%T = > 90\%$

Proposal: Dual side patterning × Fine mesh pattern electrode

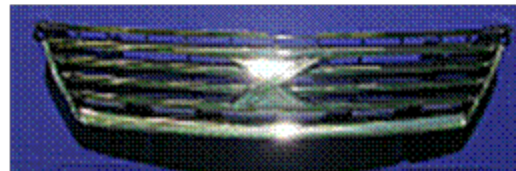
Touch panel functionality  cost  in an indium free × wet process

Plating on Glass

Conventional Plating on Plastics



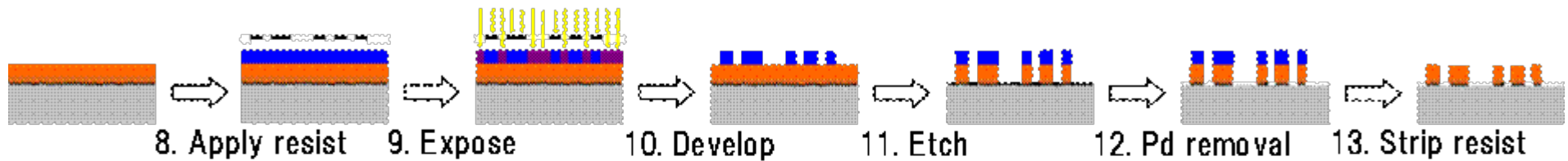
Decorative



Electronic

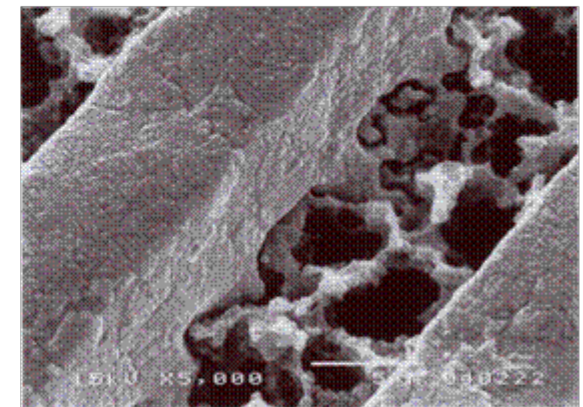
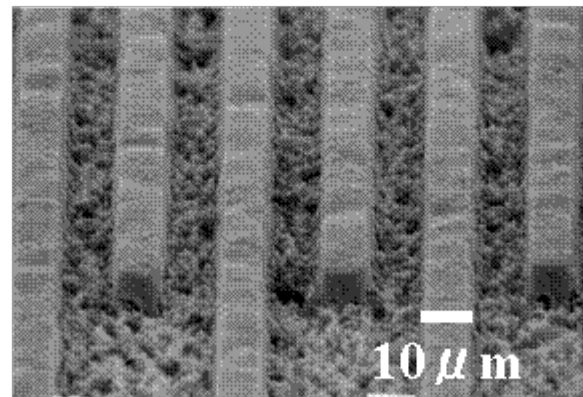


Conventional Patterning



Problems

- Too many steps
- Rough surface:
 - limited resolution
 - high impedance @ high frequency
 - Migration risk
- Bridging (short circuit)
- Chemicals with environmental impact & toxic effects



Objectives

△ Smooth substrate-plating interfaces (for increased pattern resolution & low loss high frequency transmission)

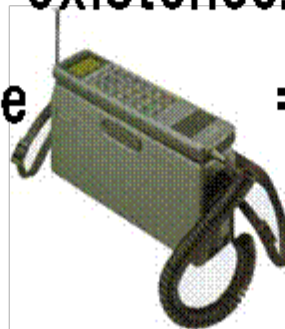
△ Precision & fine wire/structure formation

△ Lower cost

△ Increased environmental neutrality

△ Techniques to allow new or more refined functions to improve quality of existence.

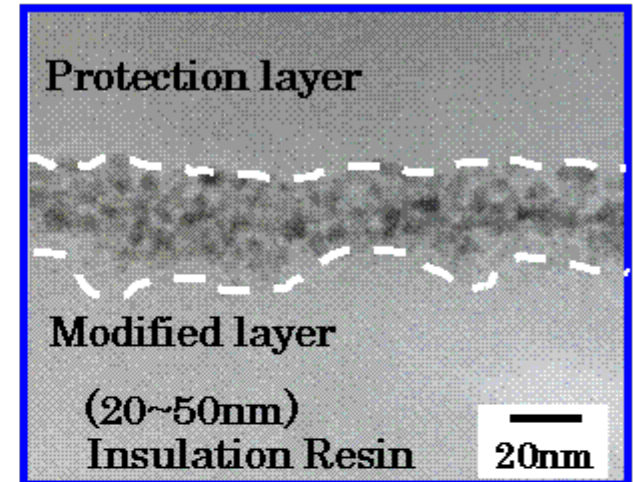
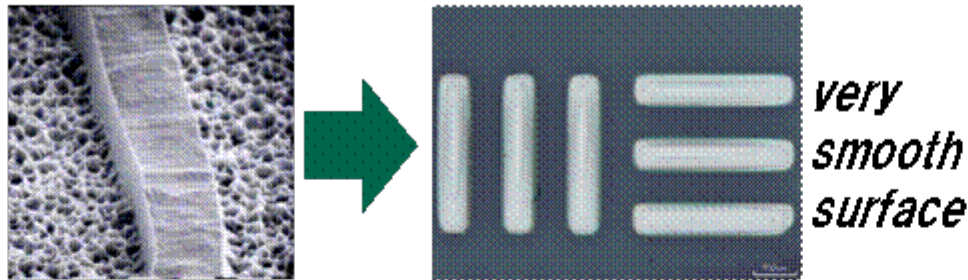
Ex: Shoulder Phone



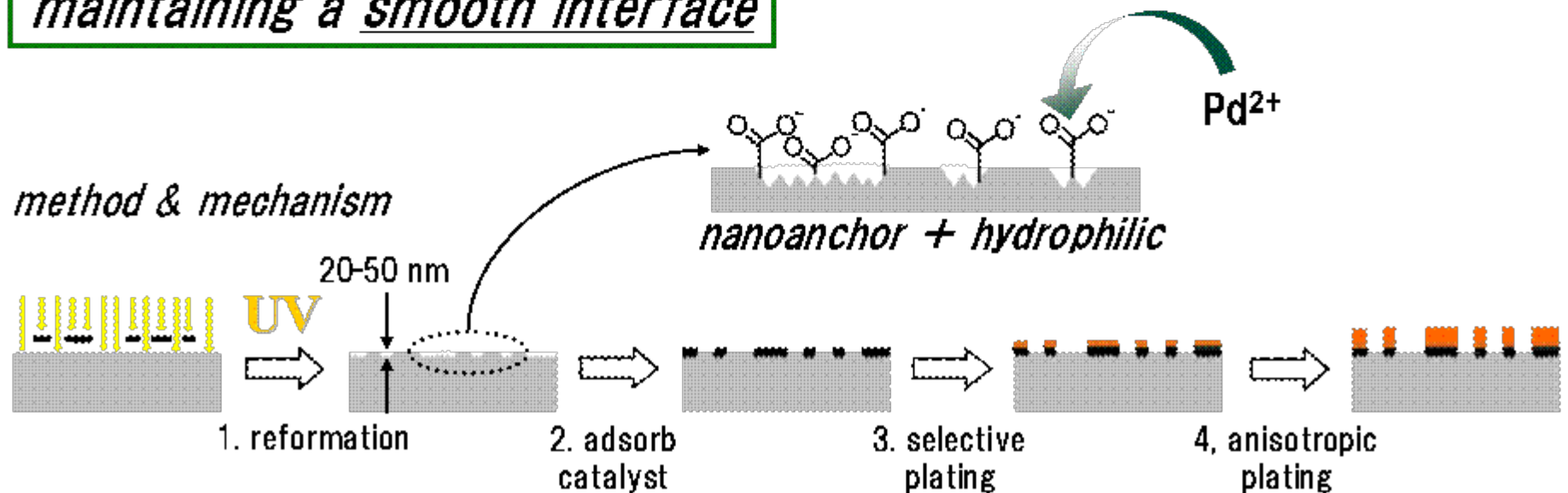
i Phone



UV Surface Refomation



*3 birds with one stone!
adhesion + patterning while
maintaining a smooth interface*



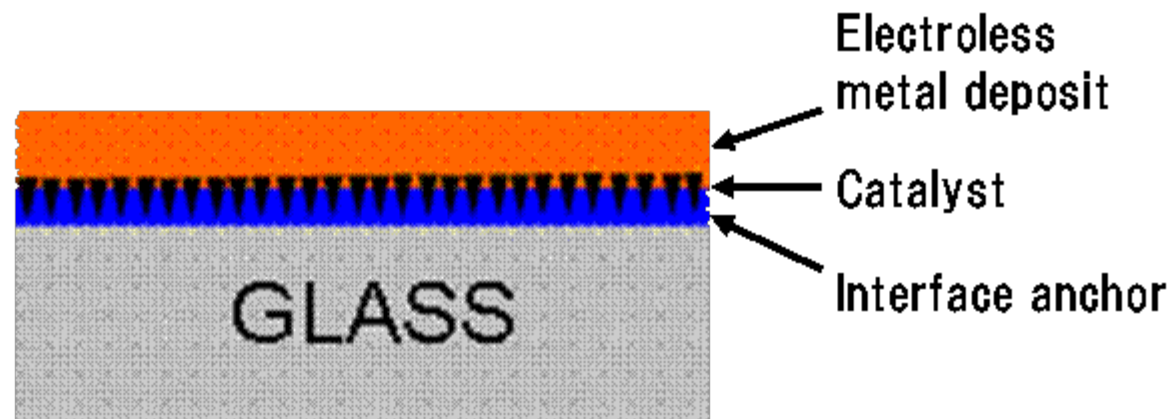
Same Model for Glass

★ Anchor Layer Formation ★

Glass surface reformation is difficult ⇒ Deposit a catalytic anchor layer

- Nano-anchor formation
- Polar material for hydrophilic surface/high metal bonding
- High adhesion fused/infused interface

Structure

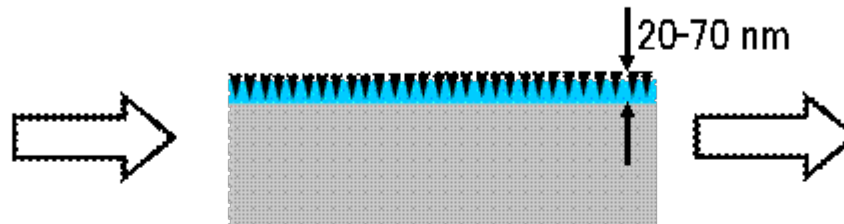


Plating on Glass

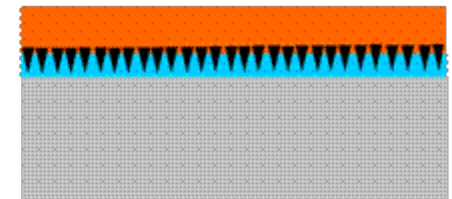
Catalytic nano-anchor
precursor coating
(solution deposition)



Nano-anchor layer ($R_a = 1 \text{ nm}$)
of 30-50% porosity containing
electroless plating catalyst



Electroless/electro plating

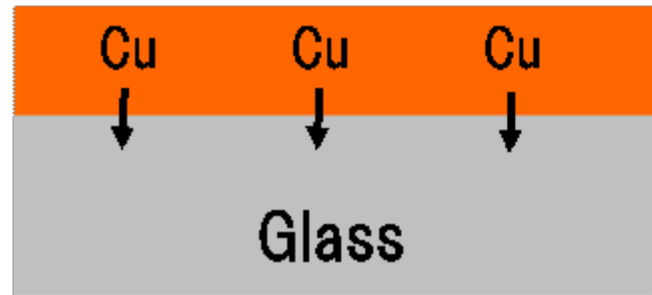


Electroless/electro plating

- Anchor layer penetration & filling
- Blister formation resistance
- Low stress deposit
- Cross cut test passed for thin films/seed layers
- Adhesion often fails for films thicker than $1 \mu\text{m}$ (electro Cu).
- Catalysts: Pd, Cu, Au
(Cu for Pd free Cu plating & Au for all gold process)
- Electroless plating: Cu (formalin), Ni (PO_3^{3+}), alloys, Ag, Au, ENIG
- Electroplating: low stress bright copper sulfate, gold

Copper Stained Glass

Electrolytic copper (5-20 μm)



thermal
infusion
350-500°C



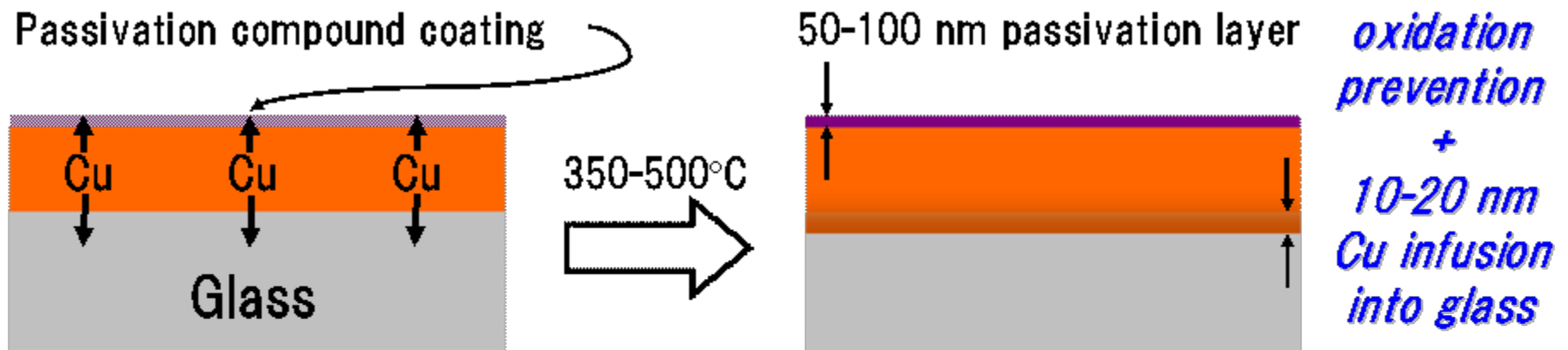
Infusion of copper into glass

- Formation for a Cu infusion layer
- Significant increase in adhesion is possible

BUT

- At high temperature severe Cu oxidation occurs
- At over 400°C, complete oxidation to CuO
- At high temperature Ni oxidation/discoloration occurs

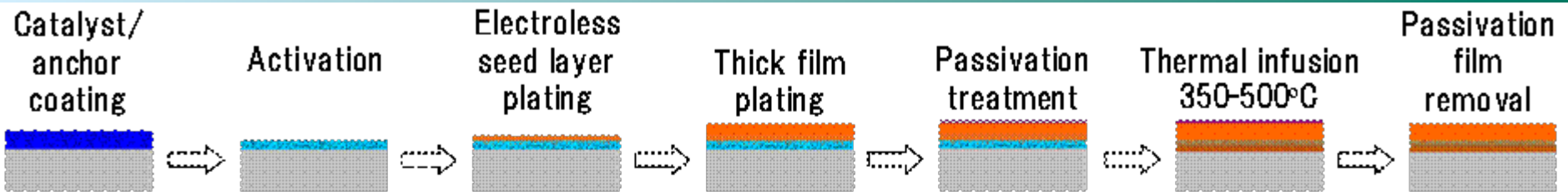
Copper/Nickel Passivation



Infusion of copper into glass

- Formation for a Cu infusion layer
- Conducting surface remains smooth
- Significant increase in adhesion (0→0.3 kN/m for Cu/Tempax)
- Oxidation does not progress beyond the passivation layer
- No discoloration of Cu or Ni at high temperature
- Easy removal of passivation film after thermal infusion

Overall Process



Example: Copper plating

Substrate: 5x5 cm Tempax glass

Catalyst: AHK1T-259 palladium catalyst (spin coat solution)

Curing: 200-500°C

Activation: Submersion in hypophosphite solution (50°C•2 min.)

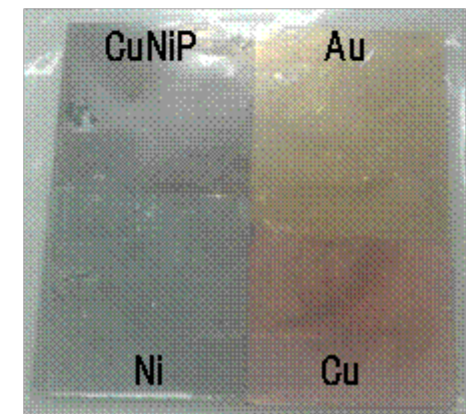
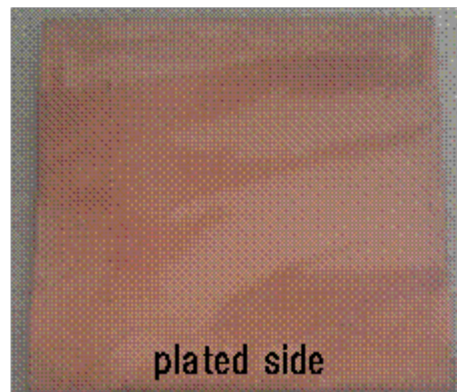
Electroless plating: 80 nm Copper

Electroplating: 17 μm Copper (acid copper @ 2.5 ASD)

Passivation: CSA spin coat

Thermal infusion: 350-500°C

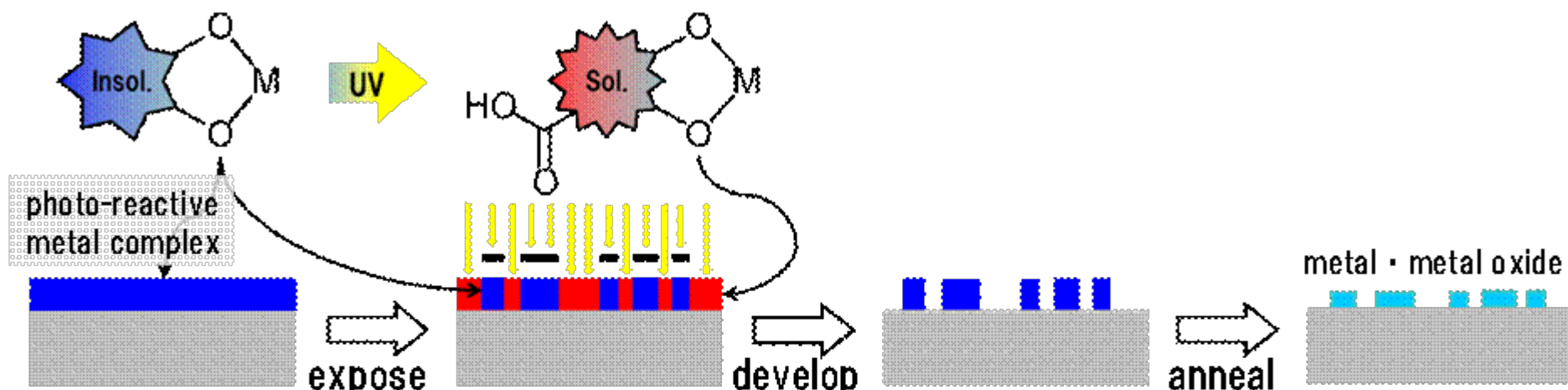
Passivation film removal: Submersion in NaOH solution (50°C•2 min.)



Direct Patterning

<5 μ m features

Photo-reactive Metal Complex



Some of the materials we have photo-patterned so far...

Complex M	→	metal · oxide	Complex M	→	metal · oxide	Complex M	→	metal · oxide
Mg	500°C	MgO	Ga	500°C	Ga ₂ O ₃	Ce	500°C	Ce ₂ O ₃
Al	500°C	Al ₂ O ₃	Ge	500°C	GeO ₂	Pr	500°C	Pr ₂ O ₃
Si	500°C	SiO ₂	Nb	500°C	Nb ₂ O ₅	Sm	500°C	Sm ₂ O ₃
Ti	500°C	TiO ₂	Ta	500°C	Ta ₂ O ₅	Eu	500°C	Eu ₂ O ₃
Hf	500°C	HfO ₂	Pd	200°C	Pd	Gd	500°C	Gd ₂ O ₃
Fe	500°C	Fe ₂ O ₃	Pd	500°C	PdO	Tb	500°C	Tb ₂ O ₃
Co	300°C	Co	In	500°C	In ₂ O ₃	Dy	500°C	Dy ₂ O ₃
Co	500°C	CoO	In	flash lamp	In	Ho	500°C	Ho ₂ O ₃
Ni	500°C	NiO	Sn	500°C	SnO ₂	Er	500°C	Er ₂ O ₃
Cu	500°C	CuO	La	500°C	La ₂ O ₃	Lu	500°C	Lu ₂ O ₃

Two-tone Patterning

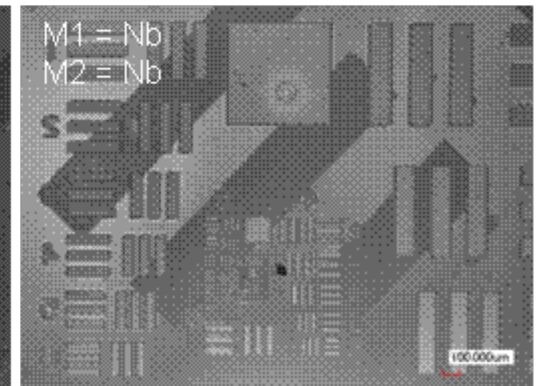
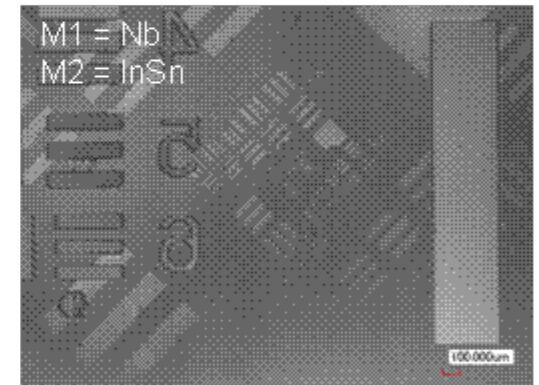
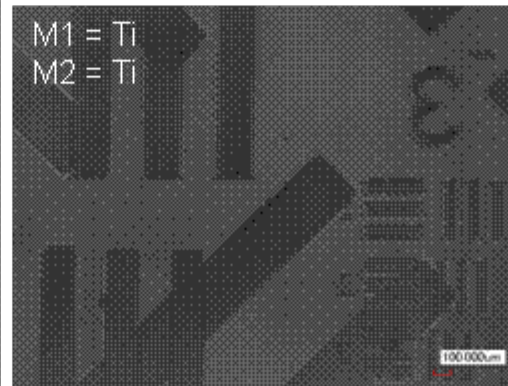
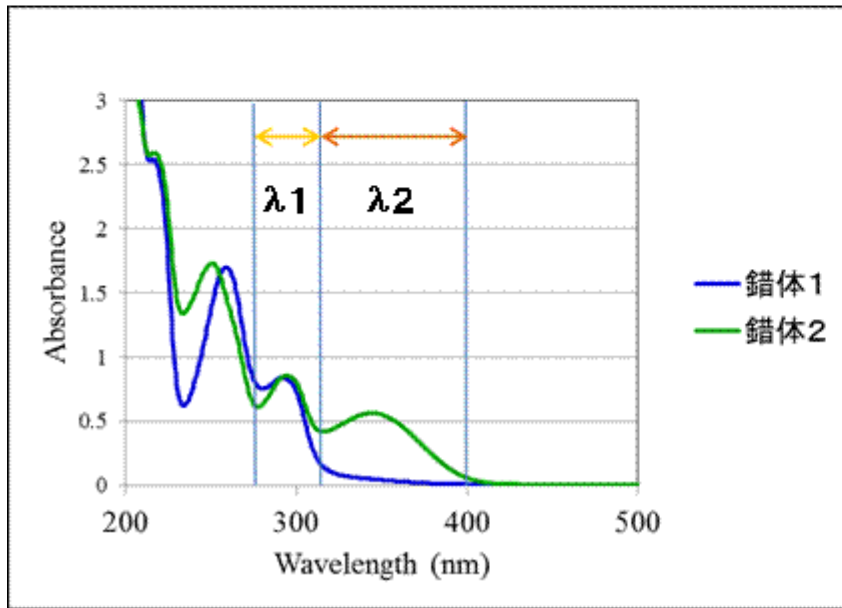
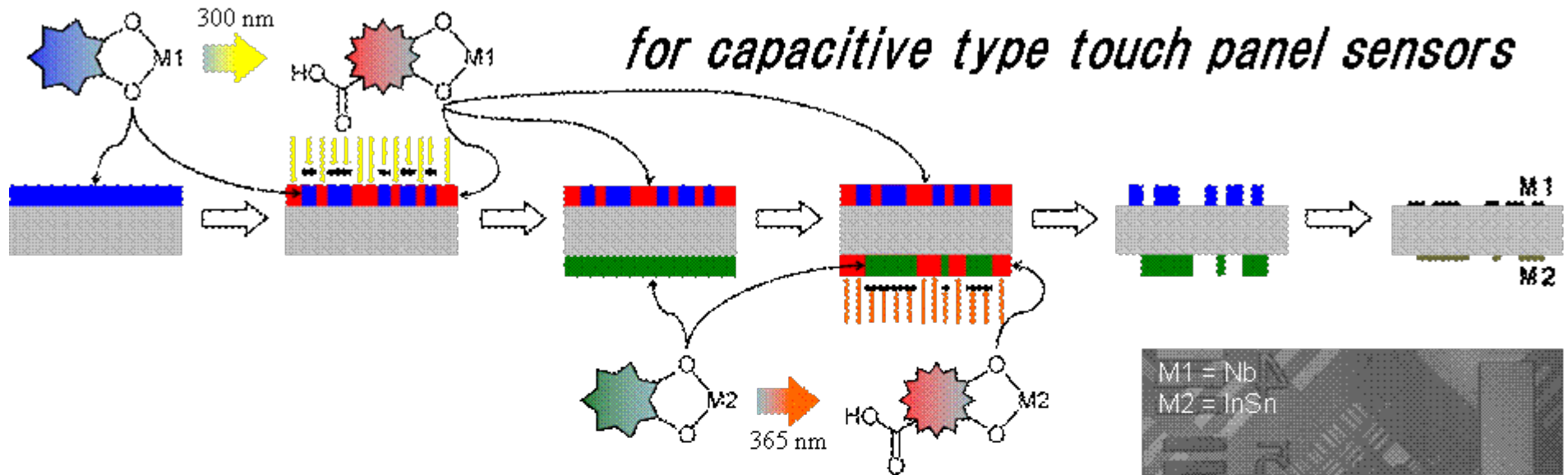
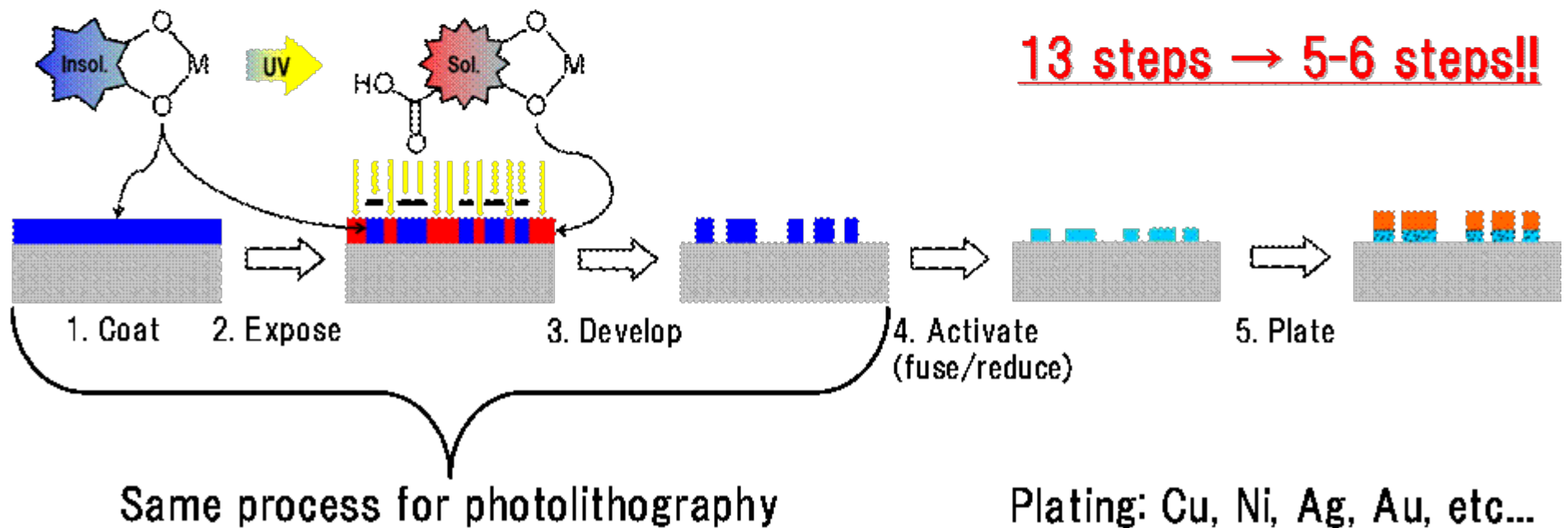


Photo-patterning + Plating System

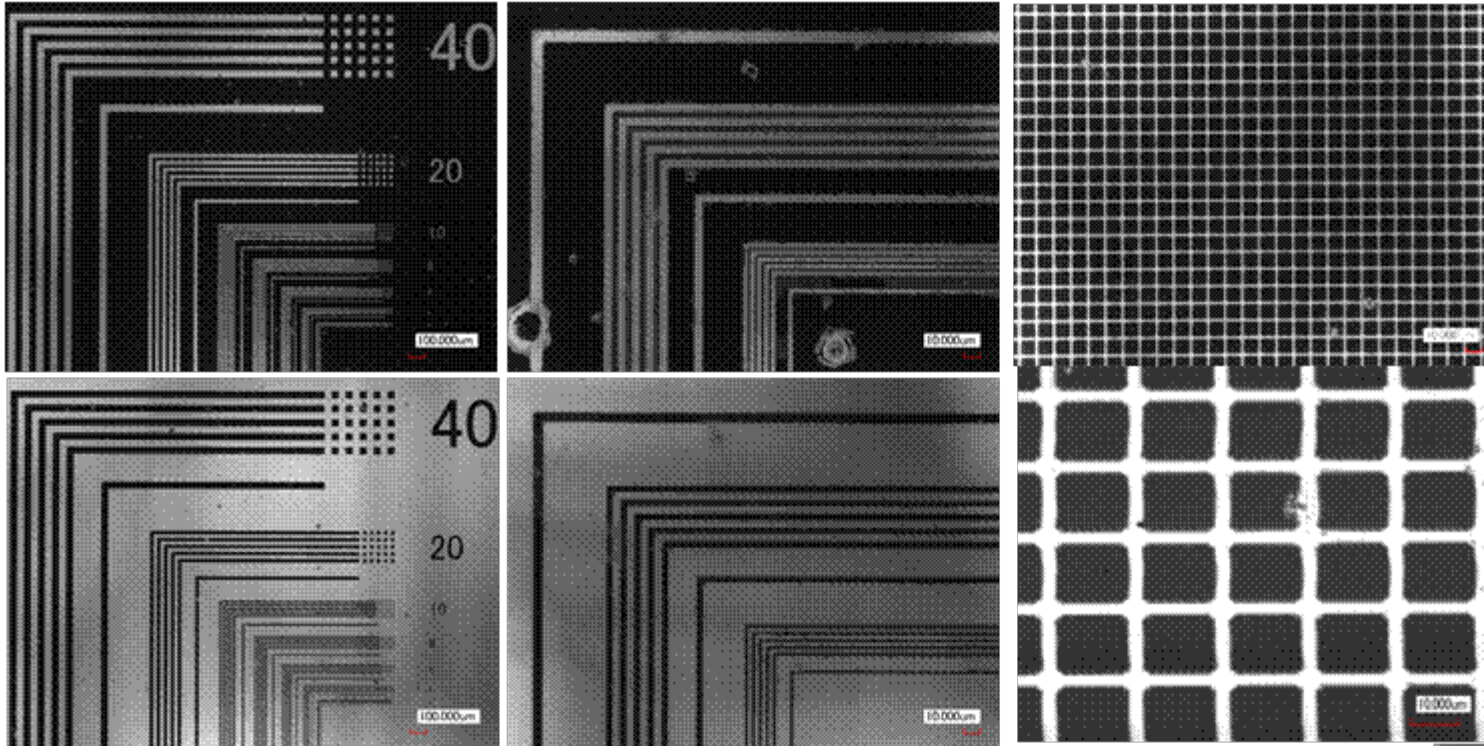
- Same apparatus as used for patterning photo resist / photolithography
- Same light source & amount of exposure
- Same aqueous developer
- No etching
- No resist stripping
- Fully additive circuit formation
- All solution processing
- High resolution (so far 400 nm features)



Palladium Patterning

L-line/trench & bump/hole: L/S = 2~100 μm on glass

Pd Mesh L/S = 1.5/10 μm

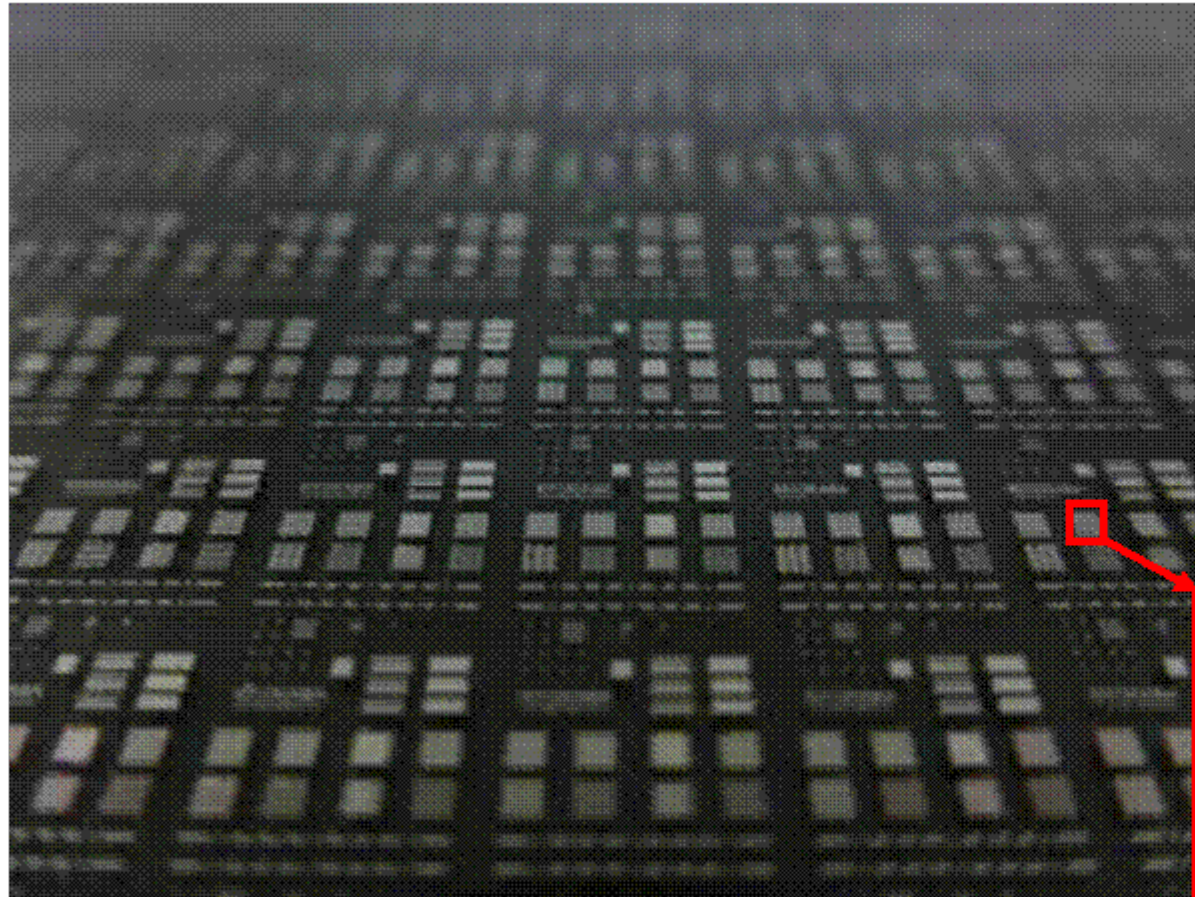


NVOC-Pd \rightarrow Pd⁰ (Positive tone)

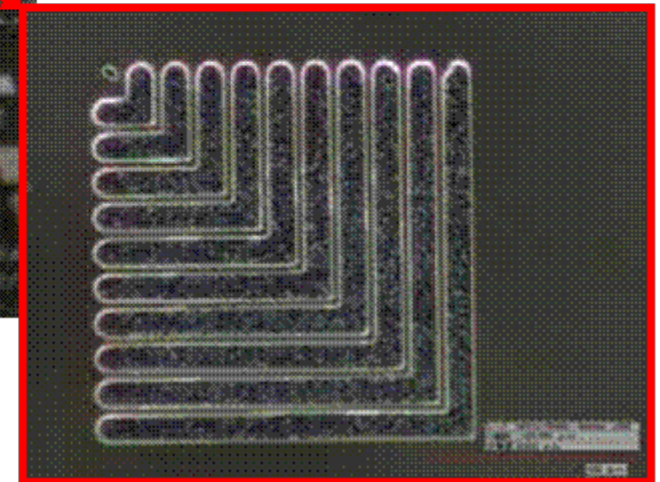
★ glass, silicon, PC, PEN ★



Direct Pattern Ni Plating

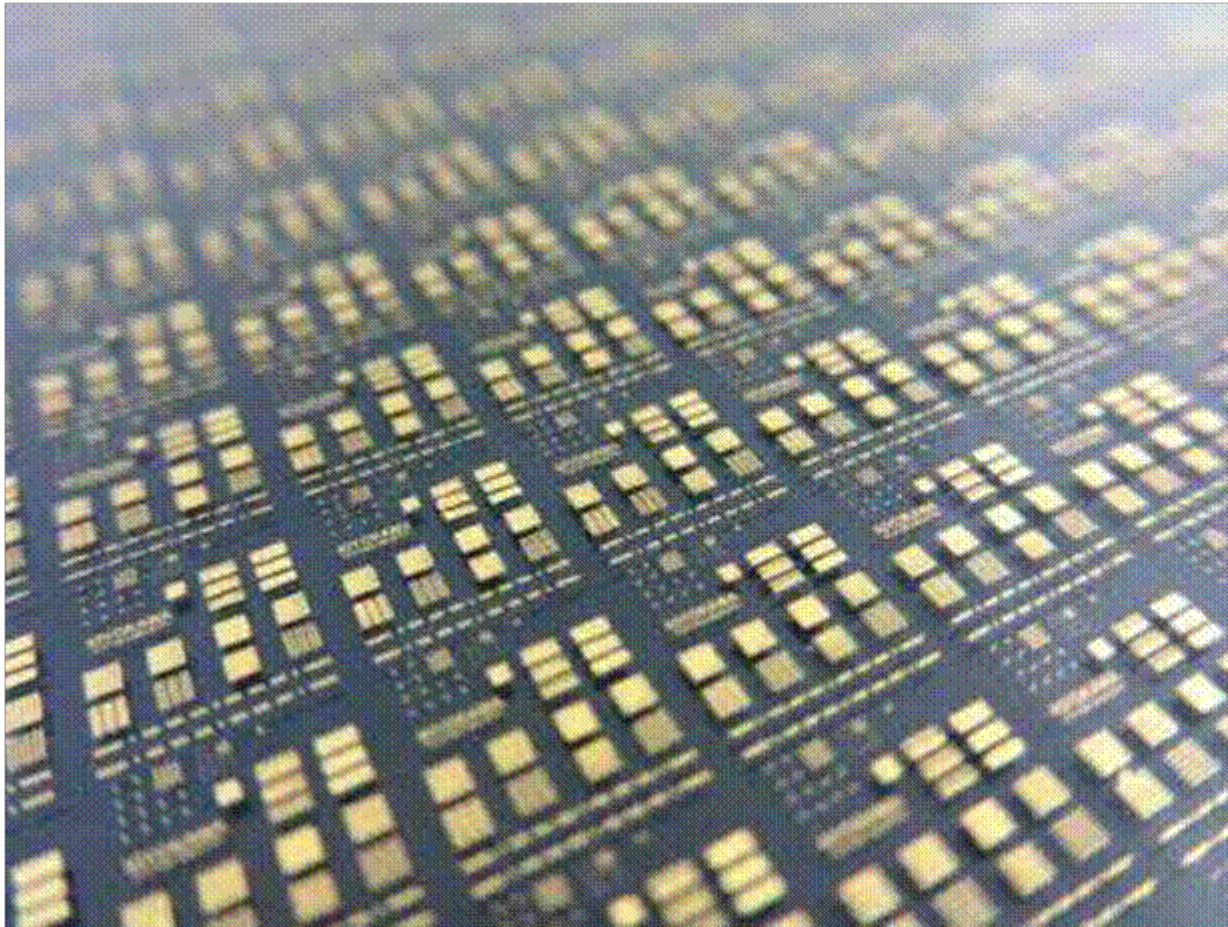


Selective nickel plating
on **TETC73-246A** pattern



On display @ Semicon Japan 2012
Dec. 5-7th at Makuhari Messe
by Kiyokawa Plating Industry Co. Ltd.

Direct Pattern ENIG Plating

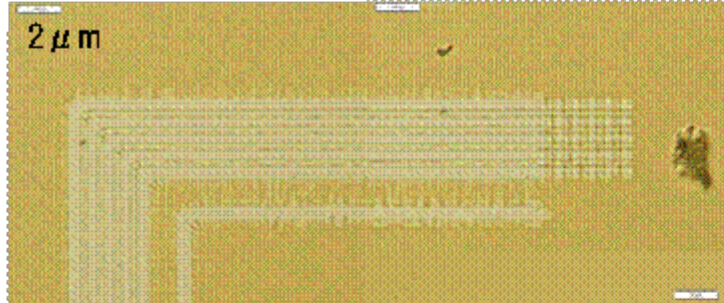


Selective
electroless nickel /
immersion gold
plating on
TETC73-246A pattern

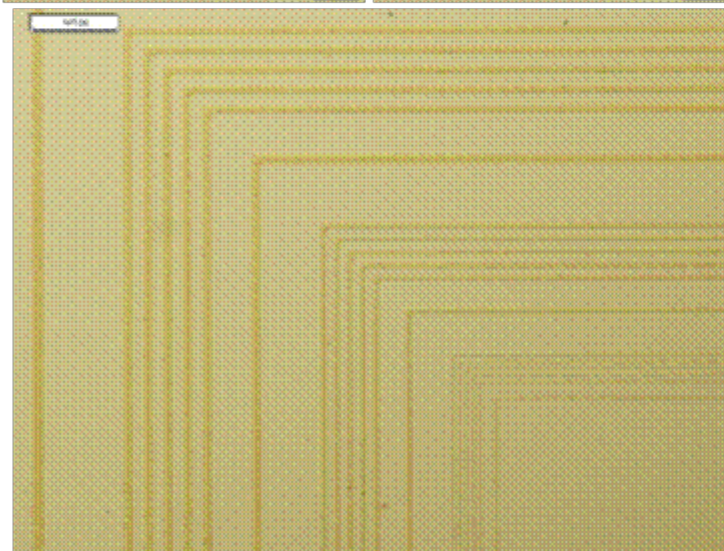
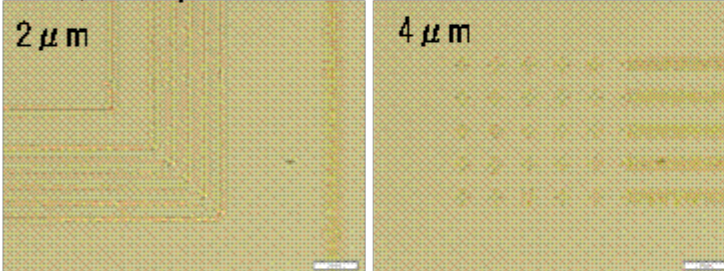
On display @ Semicon Japan 2012
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Cu Catalyst Patterning

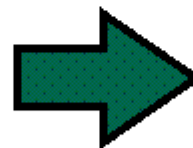
trench / hole



line / bump



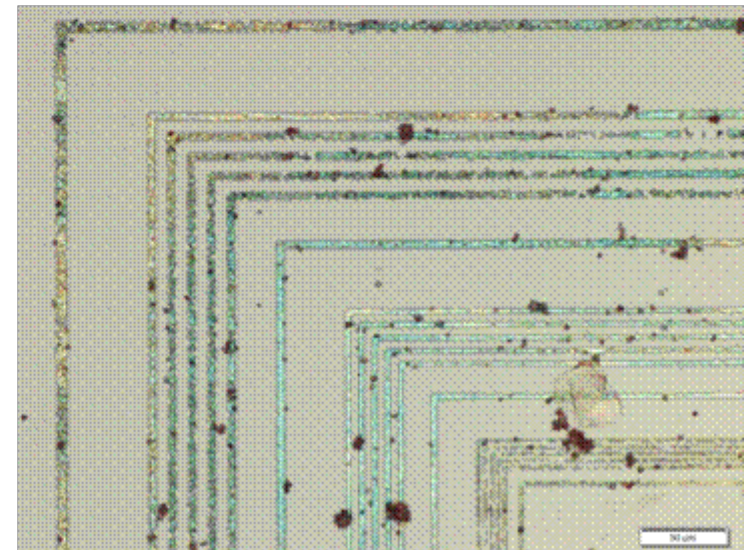
Copper plating on photopatterned copper catalyst on Tempax



6 μm

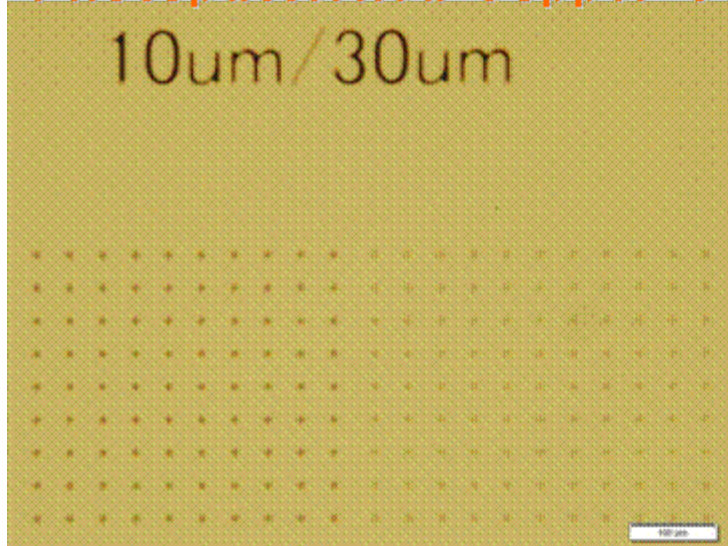
4 μm

2 μm

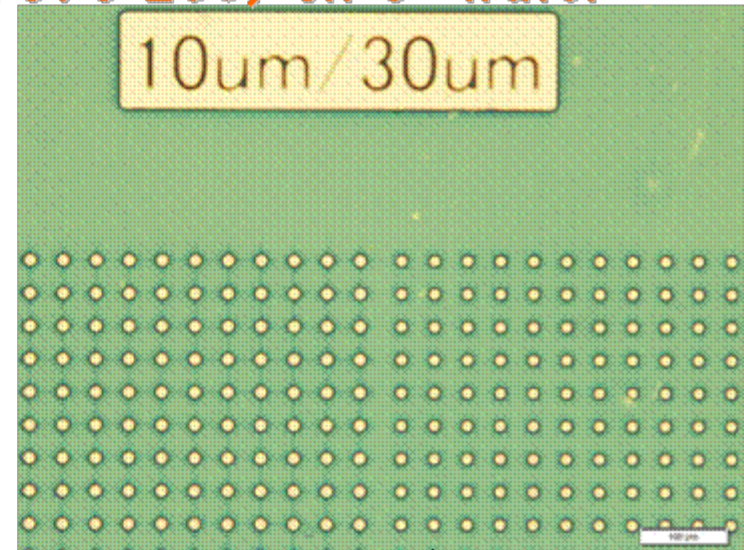


Cu Catalyst Patterning

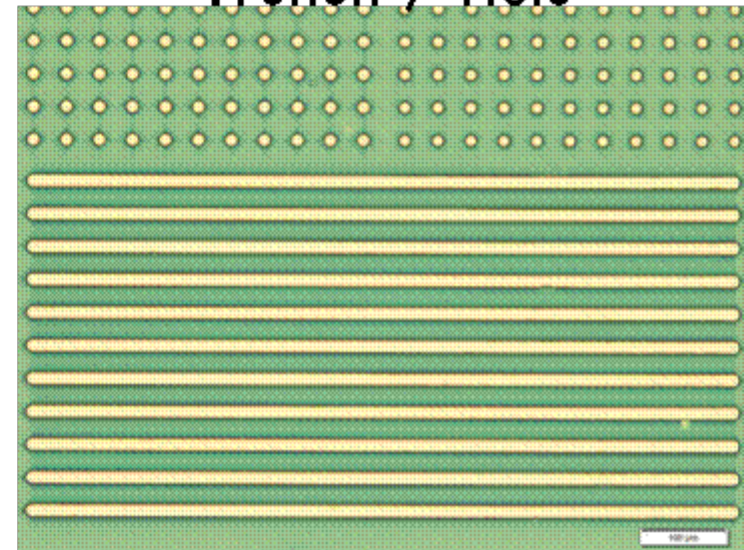
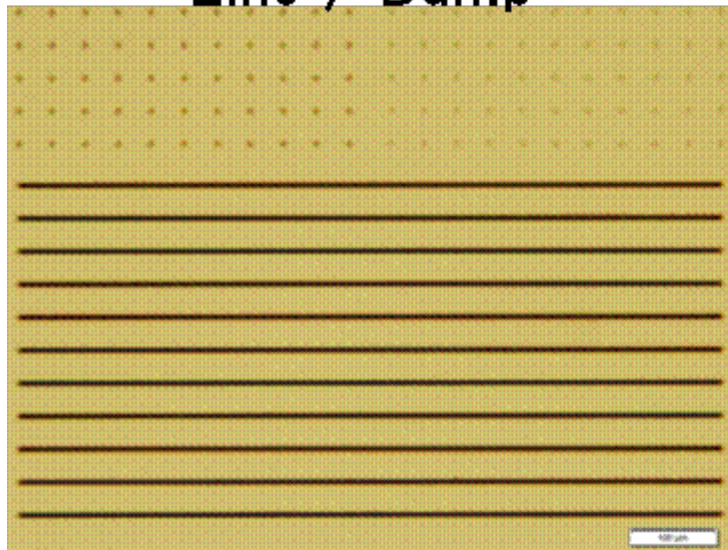
Photopatterned Copper Catalyst (BTC73-250) on 8" wafer



Line / Bump

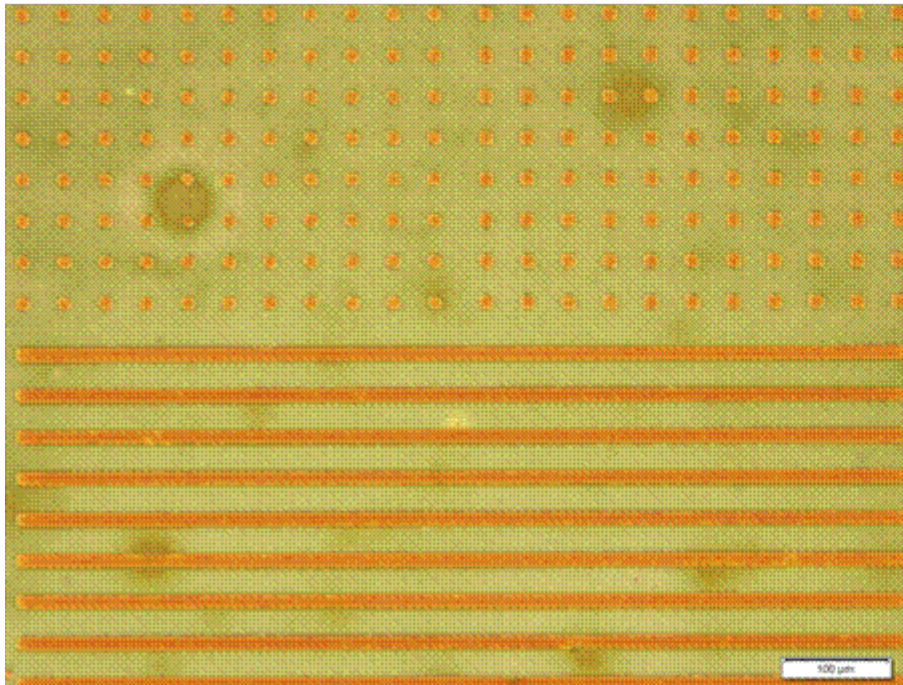


Trench / Hole

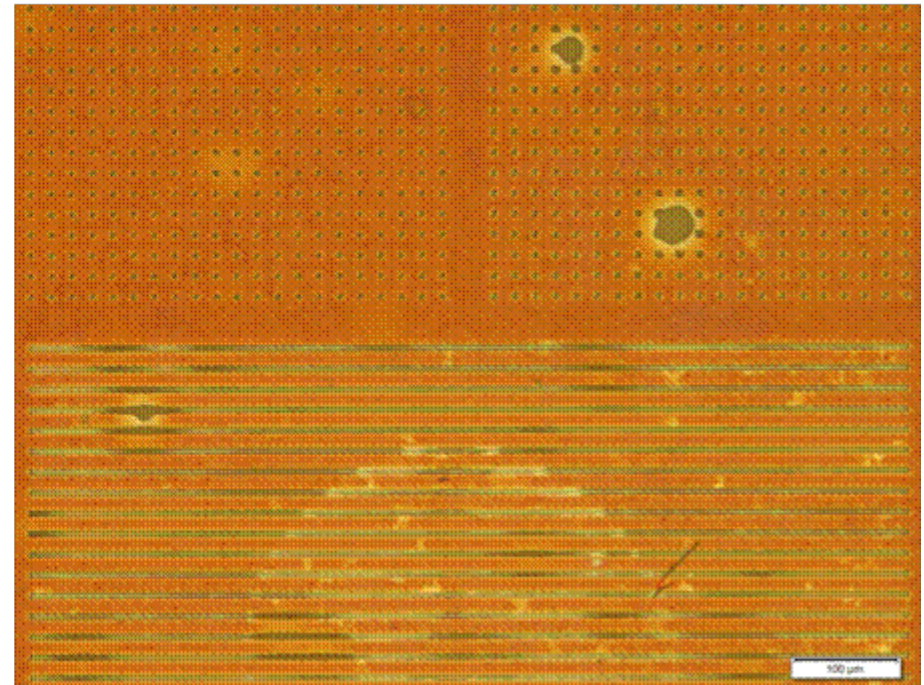


Cu Plating on Cu Catalyst

Selective Electroless Copper (PB-506) on Photopatterned Copper Catalyst (BTC73-250) on 8" Wafer



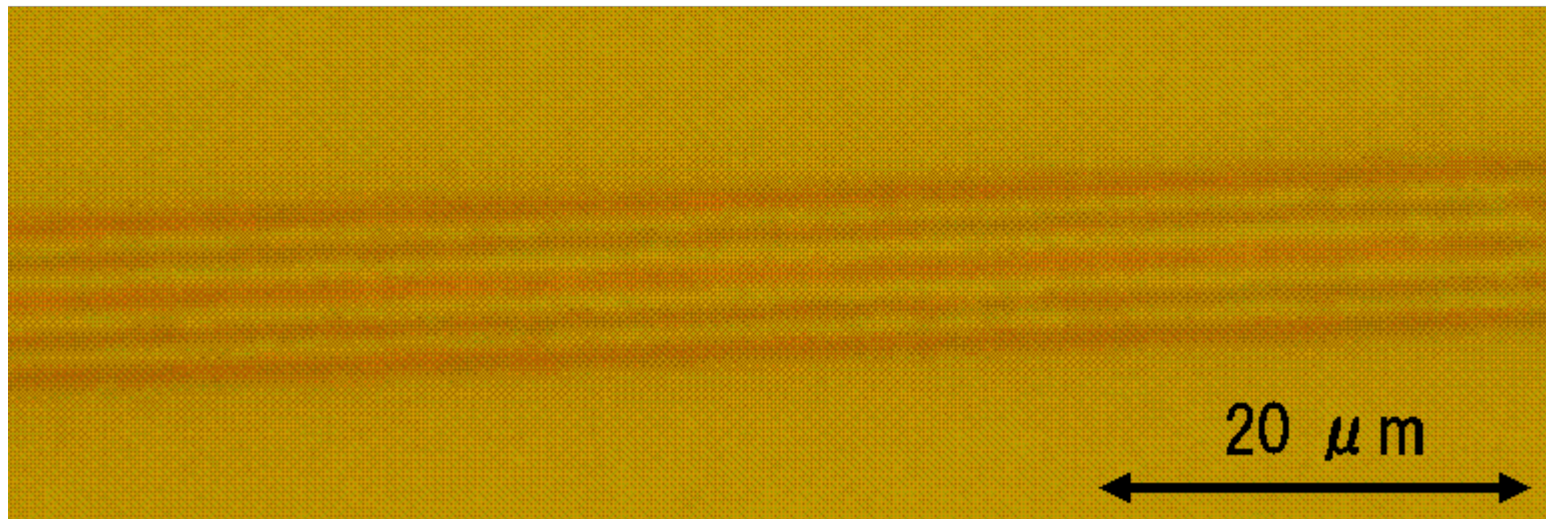
Line / Bump



Trench / Hole

Cu Catalyst Patterning

Selective Electroless Copper on Photopatterned Copper Catalyst

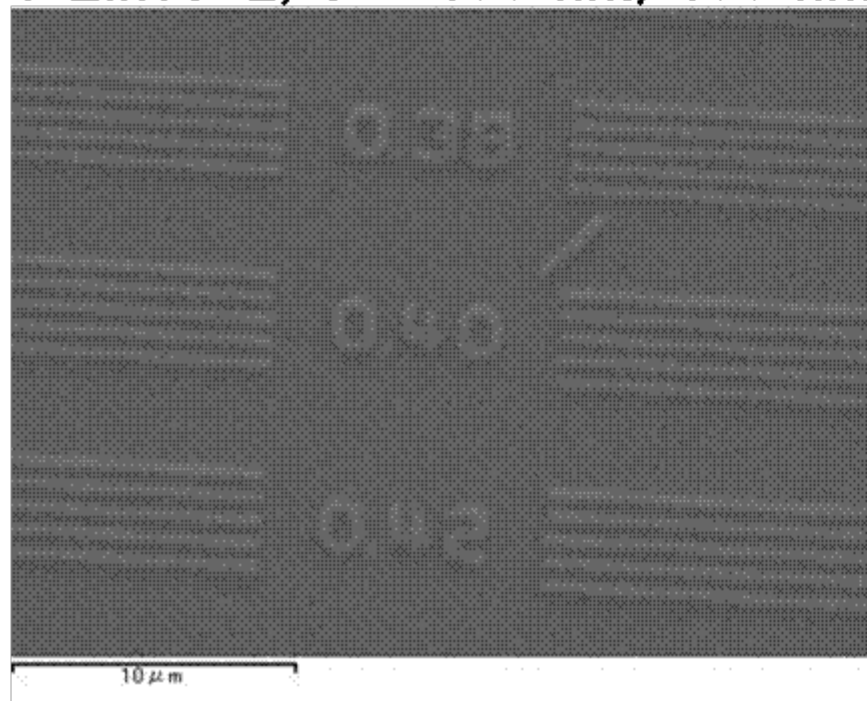


5 Lines: $L/S = 1 \mu\text{m}/1 \mu\text{m}$

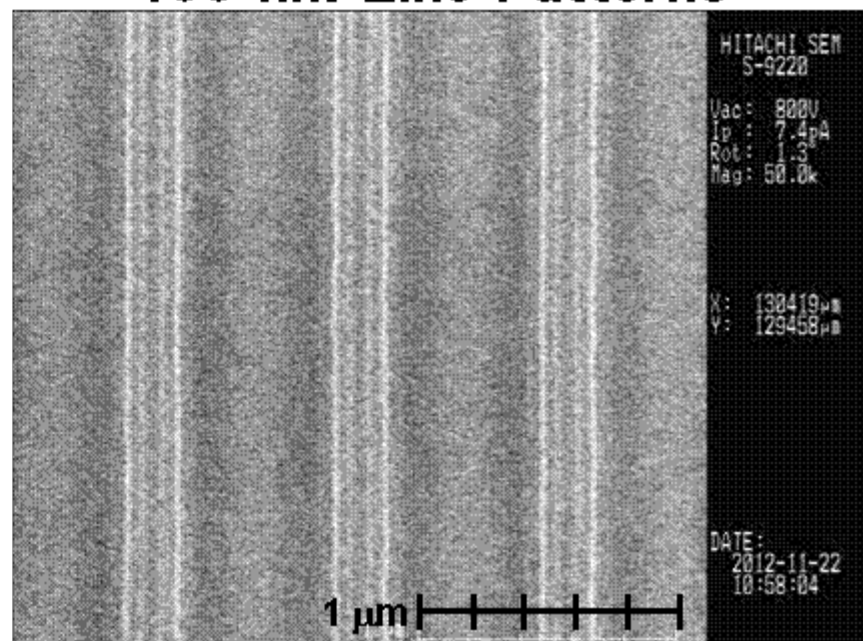
Cu Catalyst Nano-Patterning

Photopatterned Copper Catalyst (TETC73-246A)

5 Lines: $L/S = 400 \text{ nm}/400 \text{ nm}$

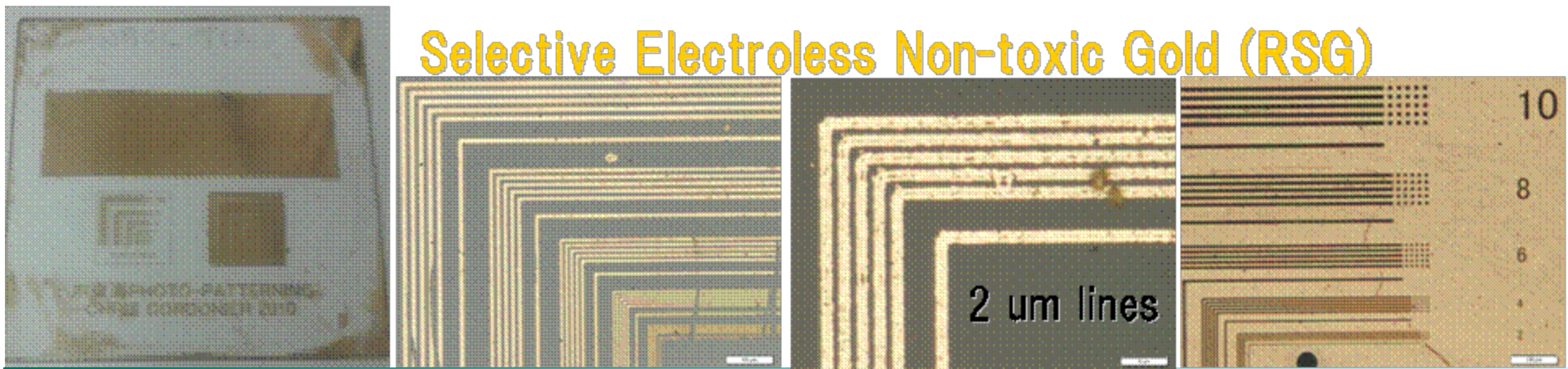
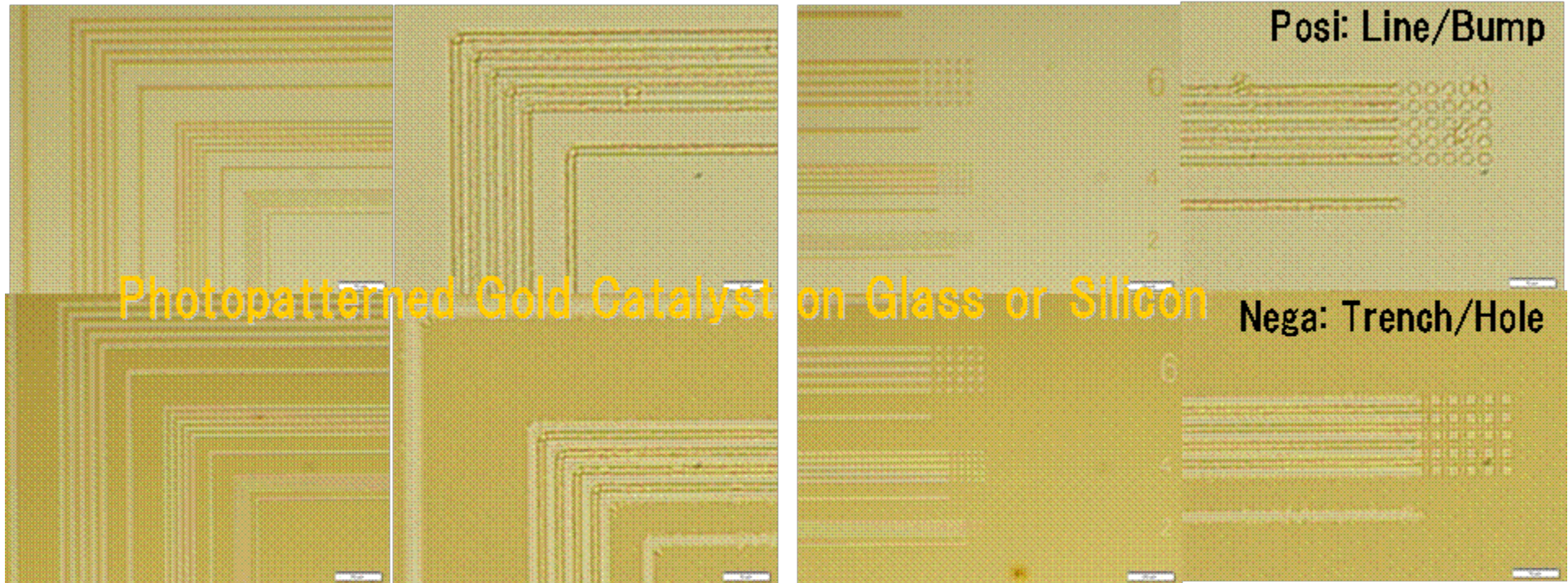


400 nm Line Patterns



Patterned by
Tokyo Ohka Kogyo

Bio-compatible All-Au Plating



Cyanide Free Gold Plating: RSG

Weakly acidic, non-toxic gold plating bath

for medical & bio device fabrication

Characteristics of RSG



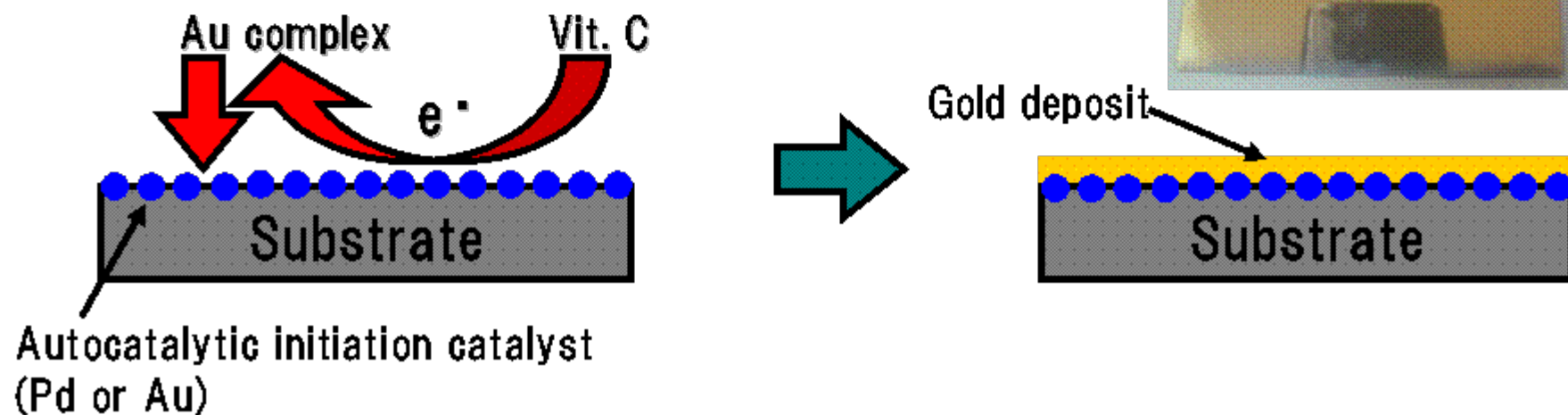
- Can be designed to function without use of toxic, hazardous, or environmentally harmful substances. No use of cyanide.
- Complexants and additives can be selected from amino acids, vitamins, minerals, antibiotics and other pharmaceutical intermediates.
- Reduced by vitamin C.
- Compatible with direct pattern plating methods described here, UV surface modification of resin method described by Koto Electric, with electrolytic reduction, or as immersion gold.
- Can be used over a wide pH range (4–14).
- Still in developmental stage, so deposit characteristics are not yet fully understood.
- Autocatalytic reaction initiation by gold or palladium catalyst.
- Simple gold(I) complex synthesis via sodium tetrachloroaurate(III). Easy isolation in a pure form free of chloride if necessary.
- More stable than gold sulfite baths, & no relation to “lemon gold” baths.

“THE GOLD PLATING SOLUTION YOU CAN DRINK”

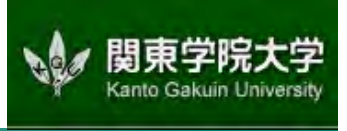
Chemical Plating

Plating bath composition/parameters

- Gold(I) complex
- Electrolyte: Potassium Citrate
- Reducing agent: Vitamin C
- Additives: Accelerator (dietary supplement/amino acid), brightener (antibiotic), leveler (food additive), surfactant (food/cleanser additive)
- pH: 4-14
- Temperature: 70-85°C
- Deposition rate: Depends on additives and requirements



Summary



△ High definition photo-pattern catalyst



Direct pattern plating

△ **Submicron metal structures** (resolution limited by optical equipment) With diffraction patterns; nano level

△ Dual side & 3D patterning ⇒ **Simplified 2-side processes**
⇒ **Stacked multi-layer structures**

△ Electroless palladium-free copper & bio-compatible all-gold

△ Plating on smooth surface / smooth interfaces

△ Fine metal mesh as a transparent conductor (ITO alternative)